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SEMICONDUCTOR

November 2013

FQPF9P25 — P-Channel QFET[®] MOSFET

FQPF9P25

P-Channel QFET® MOSFET

-250 V, -6 A, 620 mΩ

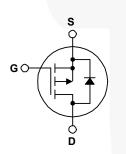
Description

This P-Channel enhancement mode power MOSFET is • -6 A, -250 V, $R_{DS(on)}$ = 620 m Ω (Max.) @ V_{GS} = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 29 nC) resistance, and to provide superior switching performance . Low Crss (Typ. 27 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

Features

- I_D = -3 A





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

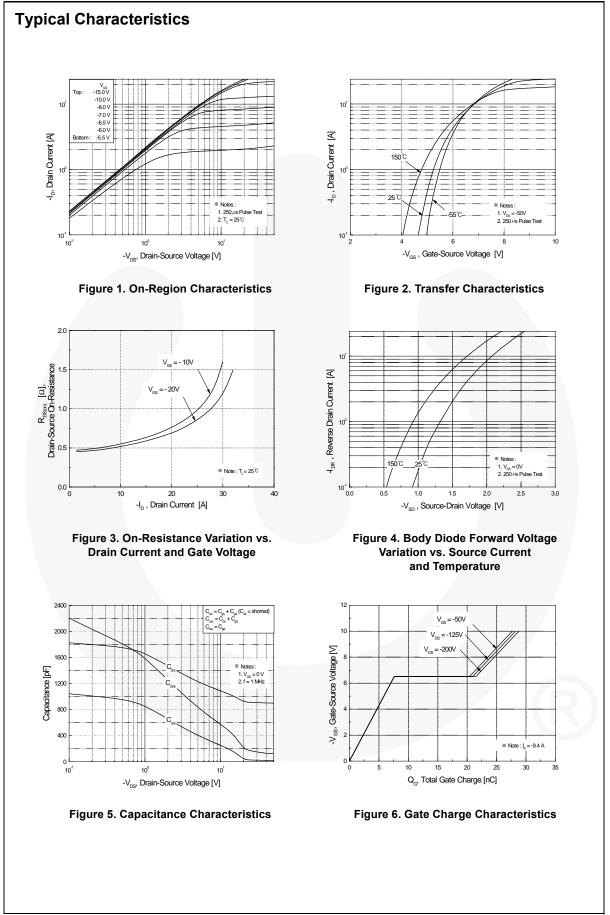
Symbol	Parameter		FQPF9P25	Unit
V _{DSS}	Drain-Source Voltage		-250	V
I _D	Drain Current - Continuous (T _C = 25°C)		-6.0	А
	- Continuous (T _C = 100°C)		-3.9	A
I _{DM}	Drain Current - Pulsed	(Note 1)	-24	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	650	mJ
I _{AR}	Avalanche Current	(Note 1)	-6.0	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		50	W
	- Derate above 25°C		0.4	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

Thermal Characteristics

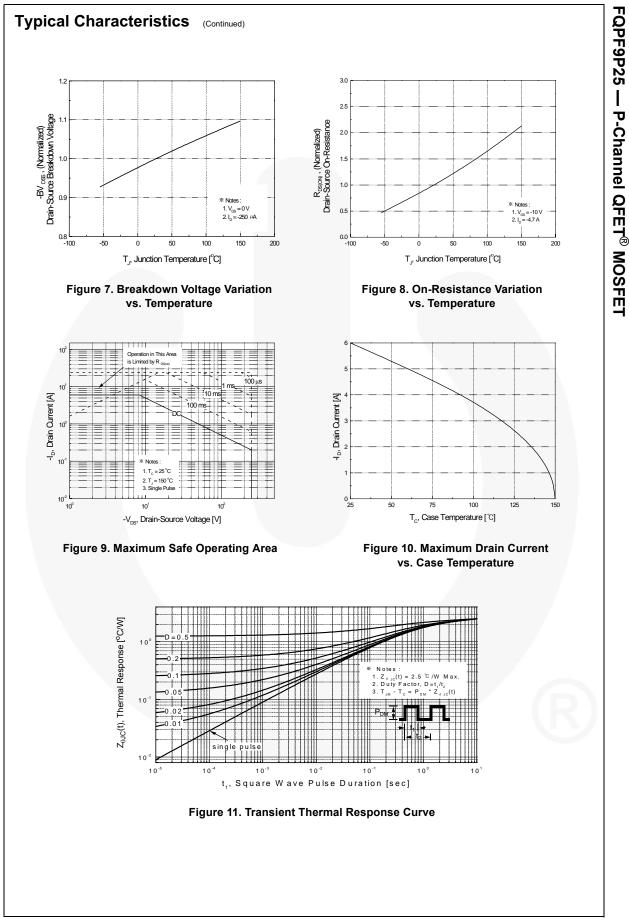
Symbol	Parameter	FQPF9P25	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

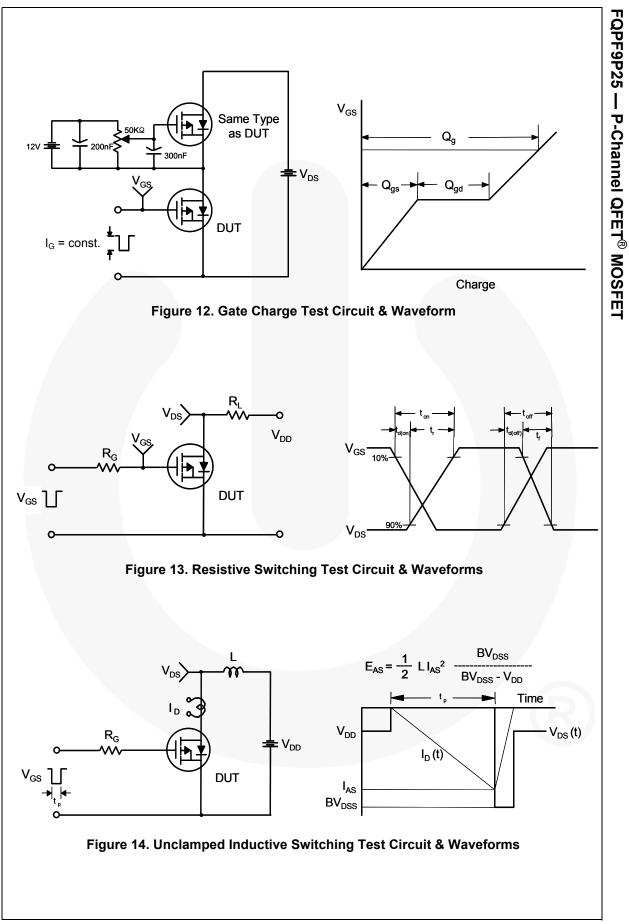
Part N	Part Number Top Mark Pac		Pack	kage Packing Method Reel		el Size	Tape Width		Quantity	
		220F Tube N/		N/A	N/A		50 units			
lectrie	cal Cha	racteristics	T _C = 25°C	C unless othe	erwise noted.					
Symbol		Parameter			Test Condition	IS	Min.	Тур.	Max.	Unit
Off Cha	aracterist	tics								
3V _{DSS}	Drain-Sou	Irce Breakdown Vol	tage	V _{GS} = 0 V, I _D = -250 μA			-250			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient		$I_D = -250 \ \mu$ A, Referenced to 25°C			C	-0.2		V/°C	
DSS				V _{DS} = -	250 V, V _{GS} = 0 V	/			-1	μA
	Zero Gate	e Voltage Drain Curr	rent	V _{DS} = -	200 V, T _C = 125	°C			-10	μA
GSSF	Gate-Bod	y Leakage Current,	Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$					-100	nA
GSSR	Gate-Bod	y Leakage Current,	Reverse	V _{GS} = 3	80 V, V _{DS} = 0 V				100	nA
On Cha	racterist	ics							I	
/ _{GS(th)}		eshold Voltage	_		/ _{GS} , I _D = -250 μ/	4	-3.0		-5.0	V
R _{DS(on)}		in-Source	_	_	10 V, I _D = -3.0 A			0.48	0.62	Ω
JFS		Forward Transconductance			40 V, I _D = -3.0 A			4.8		S
10			_	00						1
Dynam	ic Chara	cteristics								
C _{iss}	Input Cap	acitance		$V_{DS} = -$	25 V, V _{GS} = 0 V,			910	1180	pF
C _{oss}	Output Ca	utput Capacitance everse Transfer Capacitance		f = 1.0 MHz			170	220	pF	
C _{rss}	Reverse							27	35	pF
				1					1	
Switch	ing Char	acteristics								
d(on)	Turn-On [Delay Time		Vpp = -	125 V, I _D = -9.4	Δ		20	50	ns
r	Turn-On F	Rise Time		$R_G = 25$		<i>,</i> ,		150	310	ns
d(off)	Turn-Off [Delay Time		G				45	100	ns
f	Turn-Off F	all Time				(Note 4)		65	140	ns
ე ^g	Total Gate	e Charge		$V_{DS} = -$	200 V, I _D = -9.4	A,		29	38	nC
ସୁ _{gs}	Gate-Sou	rce Charge		V _{GS} = -				7.6		nC
Q _{gd}	Gate-Drai	Gate-Drain Charge		(Note 4)				14		nC
Drain-S	Source Di	iode Character	istics ar	nd Maxi	imum Rating	js				
S	Maximum	Continuous Drain-S	Source Dic	ode Forwa	ard Current				-6.0	А
SM	Maximum	Pulsed Drain-Source	ce Diode F	orward C	urrent				-24	Α
√ _{SD}	Drain-Sou	Irce Diode Forward	Voltage	$V_{GS} = 0$) V, I _S = -6.0 A				-5.0	V
rr	Reverse F	Recovery Time		$V_{GS} = 0$) V, I _S = -9.4 A,			190		ns
ე _{rr}	Reverse F	Recovery Charge		dl _F / dt	= 100 A/μs			1.45		μC
L = 28.9 m I _{SD} \leq -9.4	H, I_{AS} = -6.0 A, A, di/dt \leq 300 /	dth limited by maximum ju $V_{DD} = -50 V$, $R_G = 25 \Omega$, s $A/\mu s$, $V_{DD} \leq BV_{DSS}$, start operating temperature.	tarting T _J = 2	5°C.						

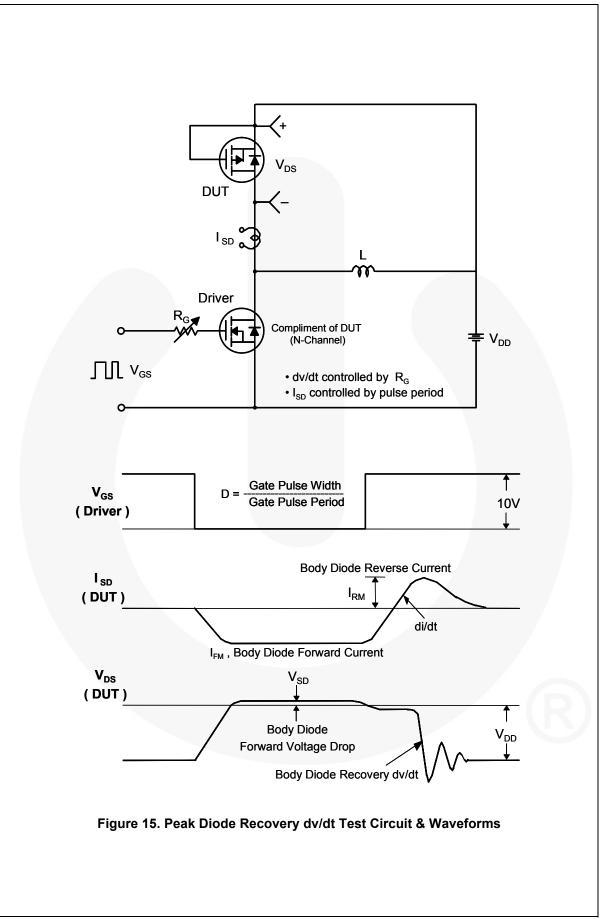
FQPF9P25 — P-Channel QFET[®] MOSFET

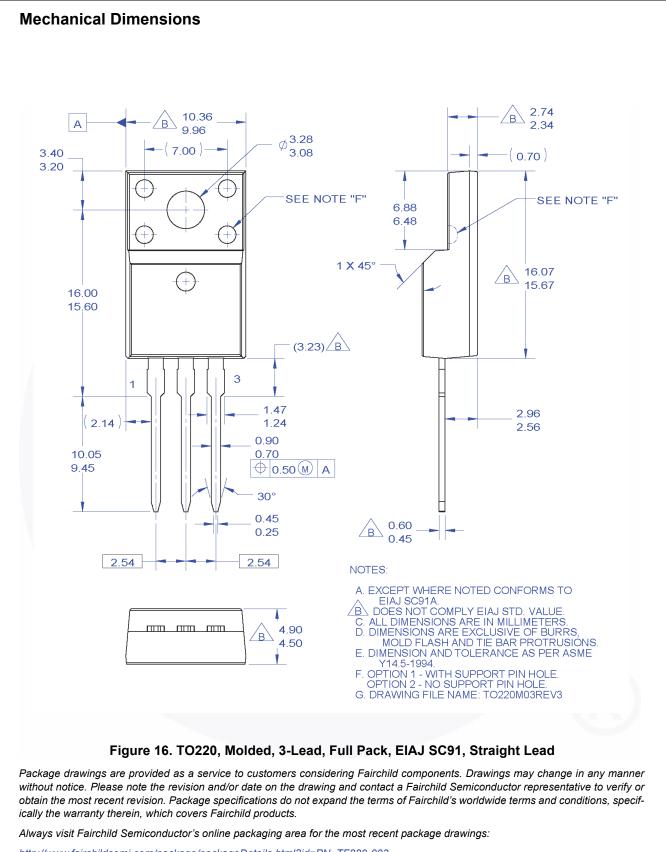


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